IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: GATE OXIDES AND METHODS OF FORMING

Docket No.: 1303.021US1
Filed: August 30, 2001
Examiner: Walter Lindsay
Customer No.: 21186

Serial No.: 09/944,981
Due Date: October 14, 2004
Group Art Unit: 2812
Confirmation No.: 1912

Commissioner for Patents
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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Kyrsti Ryan
Name

Kyrsti Ryan
Signature

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COMMUNICATION CONCERNING RELATED APPLICATION(S)

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Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/052983 6767795	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO3 FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS
10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/163686	June 5, 2002	1303.059US1	A METHOD INCLUDING FORMING GATE DIELECTRICS HAVING MULITPLE LANTHANIDE OXIDE LAYERS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA

			OXIDATION
10/219878 6790791	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn-Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAlxOy DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO4 FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
09/779959	February 9, 2001		
09/838335	April 20, 2001		
09/881408	June 13, 2001		
09/908767	July 18, 2001		

10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/863953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/930184	August 31, 2004	1303.021US2	GATE OXIDES AND METHODS OF FORMING
10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

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Date 10-14-04 By _____
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Name Kyrsthn Ryan

Signature _____